

SILICON CONTROLLED RECTIFIER

Qualified per MIL-PRF-19500/ 276

Devices

Qualified Level

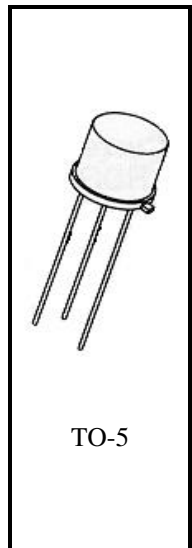
2N2323	2N2324	2N2326	2N2328	
2N2323S	2N2324S	2N2326S	2N2328S	2N2329
2N2323A	2N2324A	2N2326A	2N2328A	2N2329S
2N2323AS	2N2324AS	2N2326AS	2N2328AS	

JAN
JANTX
JANTXV

MAXIMUM RATINGS

Ratings	Sym	2N2323,S/ 2N2323A,S	2N2324,S/ 2N2324A,S	2N2326,S/ 2N2326A,S	2N2328,S/ 2N2328A,S	2N2329,S	Unit	
Reverse Voltage	V _{RM}	50	100	200	300	400	Vdc	
Working Peak Reverse Voltage	V _{RM}	75	150	300	400	500	Vpk	
Forward Blocking Voltage	V _{F BXM}	50 ^(3/4)	100 ^(3/4)	200 ^(3/4)	300 ^(3/4)	400 ⁽³⁾	Vpk	
Average Forward Current ⁽¹⁾	I _O	0.22						Adc
Forward Current Surge Peak ⁽²⁾	I _{FSM}	15						Adc
Cathode-Gate Current	V _{KGM}	6						Vpk
Operating Temperature	T _{OP}	-65 to +125						°C
Storage Junction Temp	T _{STG}	-65 to +150						°C

- 1) This average forward current is for an ambient temperature of 80°C and 180 electrical degrees of conduction.
- 2) Surge current is non-recurrent. The rate of rise of peak surge current shall not exceed 40 A during the first 5 μs after switching from the 'off' (blocking) to the 'on' (conducting) state. This is measured from the point where the thyristor voltage has decayed to 90% of its initial blocking value.
- 3) Gate connected to cathode through 1,000 ohm resistor.
- 4) Gate connected to cathode through 2,000 ohm resistor.



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
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SUBGROUP 2 TESTING

Reverse Blocking Current				
R ₂ = 1 kμ	2N2323 thru 2N2329 2N2323S thru 2N2329S			
R ₂ = 2 kμ	2N2323A thru 2N2328A 2N2323AS thru 2N2328AS			
V _R = 50 Vdc	2N2323, S, A, AS	I _{R BX1}	10	μAdc
V _R = 100 Vdc	2N2324, S, A, AS			
V _R = 200 Vdc	2N2326, S, A, AS			
V _R = 300 Vdc	2N2328, S, A, AS			
V _R = 400 Vdc	2N2329, S,			

